

Tanemasa Asano

List of Publications by Year in descending order

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| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | Evaluation of Temperature at SiC Surface During Pulsed Excimer Laser Irradiation. , 2021, , . | | 0 |
| 2 | Study of Laser Ablation Slits in Stress Reduced Embedded Die Substrate Fabricated for Heterogeneous Integration. , 2021, , . | | 0 |
| 3 | Fabrication of a bonded LNOI waveguide structure on Si substrate using ultra-precision cutting. Japanese Journal of Applied Physics, 2020, 59, SBBD03. | 1.5 | 12 |
| 4 | Demonstration of GaN/LiNbO3 Hybrid Wafer Using Room-Temperature Surface Activated Bonding. ECS Journal of Solid State Science and Technology, 2020, 9, 045005. | 1.8 | 8 |
| 5 | Evaluation of Residual Stress of Embedded Die Substrate with Hollow Structure for Heterogeneous Integration. , 2020, , . | | 1 |
| 6 | Ultrathin adhesive layer between LiNbO3 and SiO2 for bonded LNOI waveguide applications. Japanese Journal of Applied Physics, 2019, 58, SJJE06. | 1.5 | 9 |
| 7 | Formation of low resistance contacts to p-type 4H-SiC using laser doping with an Al thin-film dopant source. Japanese Journal of Applied Physics, 2019, 58, SDDF13. | 1.5 | 4 |
| 8 | High-Concentration, Low-Temperature, and Low-Cost Excimer Laser Doping for 4H-SiC Power Device Fabrication. Materials Science Forum, 2019, 963, 403-406. | 0.3 | 1 |
| 9 | Analysis of square-law detector for high-sensitive detection of terahertz waves. Journal of Applied Physics, 2019, 125, 174506. | 2.5 | 12 |
| 10 | Residual Stress in Lithium Niobate Film Layer of LNOI/Si Hybrid Wafer Fabricated Using Low-Temperature Bonding Method. Micromachines, 2019, 10, 136. | 2.9 | 15 |
| 11 | Impact of subthreshold slope on sensitivity of square law detector for high frequency radio wave detection. Japanese Journal of Applied Physics, 2019, 58, SBBL05. | 1.5 | 5 |
| 12 | Quantitative Discussion on Sensitivity to Terahertz Waves of Detectors Made of MOSFET and High-Electron Mobility Transistor. , 2019, , . | | 0 |
| 13 | Low-temperature, high-concentration laser doping of 4H-SiC for low contact resistance. , 2019, , . | | 1 |
| 14 | Highly sensitive terahertz-wave arrayed detector using InAs-HEMT on glass for video-imaging application. , 2019, , . | | 0 |
| 15 | Effect of Subthreshold Slope on Sensitivity of MOS-HEMT Square Law Detector for THz Waves. , 2018, , . | | 1 |
| 16 | Design and Characterization of One-Sided Directional Slot Antenna for 1 THz Waves. , 2018, , . | | 0 |
| 17 | Modeling and simulation of chemical amplification photoresist to produce high-density cone-shaped micro bumps. , 2018, , . | | 0 |
| 18 | Wideband slot array antenna for 1 THz band imaging device. , 2018, , . | | 0 |

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| 19 | Evaluation of effective length of the enhanced oxidation of active oxygen produced using SrTi _x Mg _{1-x} O ₃ catalyst for low-temperature oxidation. Japanese Journal of Applied Physics, 2018, 57, 04FB09. | 1.5 | 0 |
| 20 | Room-temperature wafer bonding of LiNbO ₃ and SiO ₂ using a modified surface activated bonding method. Japanese Journal of Applied Physics, 2018, 57, 06HJ12. | 1.5 | 23 |
| 21 | Thin-film lithium niobate-on-insulator waveguides fabricated on silicon wafer by room-temperature bonding method with silicon nanoadhesive layer. Optics Express, 2018, 26, 24413. | 3.4 | 27 |
| 22 | Increased doping depth of Al in wet-chemical laser doping of 4H-SiC by expanding laser pulse. Materials Science in Semiconductor Processing, 2017, 70, 193-196. | 4.0 | 7 |
| 23 | Investigation of the interface between LiNbO ₃ and Si wafers bonded by laser irradiation. Japanese Journal of Applied Physics, 2017, 56, 088002. | 1.5 | 16 |
| 24 | Surface activated wafer bonding of LiNbO ₃ and SiO ₂ /Si for LNOI on Si. , 2017, , . | | 0 |
| 25 | InAs MOS-HEMT power detector for 1.0 THz on quartz glass. , 2017, , . | | 4 |
| 26 | Time evolution of strain distribution under bonding pad during ultrasonic wire-bonding at 200°C. , 2017, , . | | 1 |
| 27 | Time evolution of strain distribution during ultrasonic bonding of Cu wire: Impact of bonding temperature. , 2017, , . | | 0 |
| 28 | Dynamic Strain of Ultrasonic Cu and Au Ball Bonding Measured In-Situ by Using Silicon Piezoresistive Sensor. , 2017, , . | | 4 |
| 29 | Enhanced oxidation of Si using low-temperature oxidation catalyst SrTi _x Mg _{1-x} O ₃ . Japanese Journal of Applied Physics, 2016, 55, 06GJ05. | 1.5 | 3 |
| 30 | Bonding dynamics of compliant microbump during ultrasonic bonding investigated by using Si strain gauge. Japanese Journal of Applied Physics, 2016, 55, 06GP22. | 1.5 | 7 |
| 31 | Al doping of 4H-SiC by laser irradiation to coated Al film and its application to junction barrier Schottky diode. Japanese Journal of Applied Physics, 2016, 55, 04ER07. | 1.5 | 4 |
| 32 | Low-temperature oxidation of 4H-SiC using oxidation catalyst SrTi _x Mg _{1-x} O ₃ . Japanese Journal of Applied Physics, 2016, 55, 108001. | 1.5 | 2 |
| 33 | Demonstration of ultraprecision ductile-mode cutting for lithium niobate microring waveguides. Japanese Journal of Applied Physics, 2016, 55, 110304. | 1.5 | 5 |
| 34 | Development and characterization of a flat laminate vapor chamber. Applied Thermal Engineering, 2016, 104, 461-471. | 6.0 | 40 |
| 35 | Sensing local dynamic strain and temperature evolution during ultrasonic bonding of microbumps. , 2016, , . | | 4 |
| 36 | Bonding of lithium niobate to silicon in ambient air using laser irradiation. Japanese Journal of Applied Physics, 2016, 55, 08RB09. | 1.5 | 5 |

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| 37 | In-situ strain measurement of ultrasonic ball bonding. , 2016, , . | | 3 |
| 38 | Nitrogen doping of 4H-SiC by KrF excimer laser irradiation in liquid nitrogen. Japanese Journal of Applied Physics, 2015, 54, 04DP02. | 1.5 | 7 |
| 39 | Room-temperature bonding mechanism of compliant bump with ultrasonic assist. , 2015, , . | | 0 |
| 40 | Room-temperature ultrasonic-bonding characteristics of compliant micro-bump investigated by ex-situ and in-situ measurements. , 2015, , . | | 0 |
| 41 | In situ observation of ultrasonic flip-chip bonding using high-speed camera. Japanese Journal of Applied Physics, 2015, 54, 030204. | 1.5 | 11 |
| 42 | Bonding of LINBO3 thin film on Si substrate using laser irradiation. , 2015, , . | | 0 |
| 43 | High-speed via hole filling using electrophoresis of Ag nanoparticles. , 2015, , . | | 0 |
| 44 | Fabrication of VGA size near-infrared image sensor using room-temperature flip-chip bonding technology. , 2014, , . | | 1 |
| 45 | Examination of residual stress measurement in electronic packages using phase-shifted sampling moiré method and X-ray images. , 2014, , . | | 1 |
| 46 | Lithium niobate ridged waveguides with smooth vertical sidewalls fabricated by an ultra-precision cutting method. Optics Express, 2014, 22, 27733. | 3.4 | 40 |
| 47 | Analysis of room-temperature bonded compliant bump with ultrasonic bonding. , 2014, , . | | 5 |
| 48 | Room-temperature bonding of heterogeneous materials for near-infrared image sensor. Japanese Journal of Applied Physics, 2014, 53, 04EB01. | 1.5 | 11 |
| 49 | Room-temperature hermetic sealing by ultrasonic bonding with Au compliant rim. Japanese Journal of Applied Physics, 2014, 53, 06JM05. | 1.5 | 20 |
| 50 | Aluminum doping of 4H-SiC by irradiation of excimer laser in aluminum chloride solution. Japanese Journal of Applied Physics, 2014, 53, 06JF03. | 1.5 | 13 |
| 51 | Effect of laser annealing using high repetition rate pulsed laser on optical properties of phosphorus-ion-implanted ZnO nanorods. Applied Physics A: Materials Science and Processing, 2014, 114, 625-629. | 2.3 | 2 |
| 52 | Room-temperature vacuum packaging using ultrasonic bonding with Cu compliant rim. , 2014, , . | | 2 |
| 53 | Phosphorus doping of 4H SiC by liquid immersion excimer laser irradiation. Applied Physics Letters, 2013, 102, . | 3.3 | 20 |
| 54 | Characteristic of pn junction formed in 4H-SiC by using excimer-laser processing in phosphoric solution. , 2013, , . | | 0 |

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| 55 | Effect of Coating Self-Assembled Monolayer on Room-Temperature Bonding of Cu Micro-Interconnects. Japanese Journal of Applied Physics, 2013, 52, 068004. | 1.5 | 2 |
| 56 | Room-Temperature Cu Microjoining with Ultrasonic Bonding of Cone-Shaped Bump. Japanese Journal of Applied Physics, 2013, 52, 04CB10. | 1.5 | 28 |
| 57 | Effect of High Repetition Pulsed Laser Annealing on Optical Properties of Phosphorus Ion-Implanted ZnO Nanorods. Advanced Materials Research, 2013, 699, 383-386. | 0.3 | 0 |
| 58 | Ultrasonic Bonding of Cone Bump for Integration of Large-Scale Integrated Circuits in Flexible Electronics. Japanese Journal of Applied Physics, 2013, 52, 05DB10. | 1.5 | 4 |
| 59 | Room-temperature high-density interconnection using ultrasonic bonding of cone bump for heterogeneous integration. , 2013, , . | | 6 |
| 60 | Phosphorus Doping into 4H-SiC by Irradiation of Excimer Laser in Phosphoric Solution. Japanese Journal of Applied Physics, 2013, 52, 06GF02. | 1.5 | 16 |
| 61 | Room Temperature Micro-joining of LSIs Using Cone Shaped Bump. Journal of the Japan Society for Precision Engineering, 2013, 79, 725-729. | 0.1 | 1 |
| 62 | Impact of Rapid Crystallization of Si Using Nickel-Metal-Induced Lateral Crystallization on Thin-Film Transistor Characteristics. Japanese Journal of Applied Physics, 2012, 51, 02BH04. | 1.5 | 3 |
| 63 | Room-Temperature Microjoining of LSI Chips on Poly(ethylene naphthalate) Film Using Mechanical Caulking of Au Cone Bump. Japanese Journal of Applied Physics, 2012, 51, 04DB04. | 1.5 | 5 |
| 64 | Effect of laser annealing on photoluminescence properties of Phosphorus implanted ZnO nanorods. Optics Express, 2012, 20, 15247. | 3.4 | 16 |
| 65 | Low-temperature bonding of LSI chips to PEN film using Au cone bump for heterogeneous integration. , 2012, , . | | 0 |
| 66 | Room temperature microjoining of qVGA class area-bump array using cone bump. , 2012, , . | | 0 |
| 67 | Room-temperature microjoining using ultrasonic bonding of compliant bump. , 2012, , . | | 11 |
| 68 | Surface protection of copper by self assembled monolayer for low-temperature chip bonding. , 2012, , . | | 0 |
| 69 | Room-Temperature Microjoining of LSI Chips on Poly(ethylene naphthalate) Film Using Mechanical Caulking of Au Cone Bump. Japanese Journal of Applied Physics, 2012, 51, 04DB04. | 1.5 | 2 |
| 70 | Impact of Rapid Crystallization of Si Using Nickel-Metal-Induced Lateral Crystallization on Thin-Film Transistor Characteristics. Japanese Journal of Applied Physics, 2012, 51, 02BH04. | 1.5 | 1 |
| 71 | Characteristics of a Novel Compliant Bump for 3-D Stacking With High-Density Inter-Chip Connections. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2011, 1, 83-91. | 2.5 | 16 |
| 72 | Supramolecular Hybrid of Gold Nanoparticles and Semiconducting Single-Walled Carbon Nanotubes Wrapped by a Porphyrin-Fluorene Copolymer. Journal of the American Chemical Society, 2011, 133, 14771-14777. | 13.7 | 46 |

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| 73 | Room-Temperature Cu-Cu Bonding in Ambient Air Achieved by Using Cone Bump. Applied Physics Express, 2011, 4, 016501. | 2.4 | 20 |
| 74 | Single-Walled Carbon Nanotube Thin Film Transistor Fabricated Using Solution Prepared with 9,9-Dioctylfluorenyl-2,7-diyl-Bipyridine Copolymer. Japanese Journal of Applied Physics, 2011, 50, 070207. | 1.5 | 7 |
| 75 | Microjoining of LSI Chips on Poly(ethylene naphthalate) Using Compliant Bump. Japanese Journal of Applied Physics, 2011, 50, 06GM05. | 1.5 | 7 |
| 76 | Ion Beam Bombardment Effect on Contacts in Solution-Processed Single-Walled Carbon Nanotube Thin Film Transistor. Japanese Journal of Applied Physics, 2011, 50, 098003. | 1.5 | 0 |
| 77 | Low-temperature bonding of LSI chips to polymer substrate using Au cone bump for flexible electronics. , 2011, , . | | 2 |
| 78 | (Invited) Self-Heating Issue of Poly-Si TFT on Glass Substrate. ECS Transactions, 2011, 37, 15-22. | 0.5 | 1 |
| 79 | Microjoining of LSI Chips on Poly(ethylene naphthalate) Using Compliant Bump. Japanese Journal of Applied Physics, 2011, 50, 06GM05. | 1.5 | 3 |
| 80 | Ion Beam Bombardment Effect on Contacts in Solution-Processed Single-Walled Carbon Nanotube Thin Film Transistor. Japanese Journal of Applied Physics, 2011, 50, 098003. | 1.5 | 3 |
| 81 | (Invited) Nano-Inkjet and Its Application to Metal-Induced Crystallization of a-Si for Poly-Si TFTs. ECS Transactions, 2010, 33, 149-156. | 0.5 | 2 |
| 82 | Room-temperature chip-stack interconnection using compliant bumps and wedge-incorporated electrodes. , 2010, , . | | 5 |
| 83 | Grain filtering in MILC and its impact on performance of n- and p-channel TFTs. , 2010, , . | | 2 |
| 84 | Effect of Argon/Hydrogen Plasma Cleaning on Electroless Ni Deposition on Small-Area Al Pads. Japanese Journal of Applied Physics, 2010, 49, 08JA05. | 1.5 | 8 |
| 85 | Fabrication of Back-Side Illuminated Complementary Metal Oxide Semiconductor Image Sensor Using Compliant Bump. Japanese Journal of Applied Physics, 2010, 49, 04DB01. | 1.5 | 34 |
| 86 | Room-Temperature Bonding Using Mechanical Caulking Effect of Compliant Bumps for Chip-Stack Interconnection. Japanese Journal of Applied Physics, 2010, 49, 04DB02. | 1.5 | 11 |
| 87 | Investigation of Enhanced Impact Ionization in Uniaxially Strained Si n-Channel Metal Oxide Semiconductor Field Effect Transistor. Japanese Journal of Applied Physics, 2010, 49, 04DC14. | 1.5 | 4 |
| 88 | Silicon Crystal Nanowires Produced by Metal-Induced Lateral Crystallization. Japanese Journal of Applied Physics, 2009, 48, 06FE03. | 1.5 | 1 |
| 89 | Analysis and Fabrication of Ampere-Force Actuated Bistable Curved Beam. Japanese Journal of Applied Physics, 2009, 48, 06FK08. | 1.5 | 4 |
| 90 | Self-Heating of Laterally Grown Polycrystalline Silicon Thin-Film Transistor. Japanese Journal of Applied Physics, 2009, 48, 03B005. | 1.5 | 6 |

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| 91 | Investigation on Characteristic Variation of Polycrystalline Silicon Thin-Film Transistor Using Laterally Grown Film. Japanese Journal of Applied Physics, 2009, 48, 03B014. | 1.5 | 9 |
| 92 | Compliant bump technology for back-side illuminated CMOS image sensor. , 2009, , . | | 2 |
| 93 | High-Density Room-Temperature 3D Chip-Stacking Using Mechanical Caulking With Compliant Bump and Through-Hole-Electrode. , 2009, , . | | 1 |
| 94 | Low-temperature solid-phase crystallization of amorphous SiGe films on glass by imprint technique. Solid-State Electronics, 2008, 52, 1221-1224. | 1.4 | 2 |
| 95 | Investigation on Bistability and Fabrication of Bistable Prestressed Curved Beam. Japanese Journal of Applied Physics, 2008, 47, 5291. | 1.5 | 41 |
| 96 | Droplet Ejection Behavior in Electrostatic Inkjet Driving. Japanese Journal of Applied Physics, 2008, 47, 5281-5286. | 1.5 | 13 |
| 97 | Monitoring Droplet Ejection and Landing in Electrospray with Electric Current and Acoustic Emission. Japanese Journal of Applied Physics, 2008, 47, 2279-2284. | 1.5 | 1 |
| 98 | Electrostatic Inkjet Printing of Carbon Nanotube for Cold Cathode Application. Japanese Journal of Applied Physics, 2008, 47, 5109-5112. | 1.5 | 10 |
| 99 | Oriented Growth of Location-Controlled Si Crystal Grains by Ni Nano-Imprint and Excimer Laser Annealing. Japanese Journal of Applied Physics, 2008, 47, 3036-3040. | 1.5 | 2 |
| 100 | Low-Temperature 3D Chip-Stacking Using Compliant Bump. , 2008, , . | | 2 |
| 101 | Inkjet-Printed Metal-Colloid-Induced Crystallization of Amorphous Silicon. Japanese Journal of Applied Physics, 2007, 46, 1263-1267. | 1.5 | 9 |
| 102 | Inkjet Printing of Nickel Nanosized Particles for Metal-Induced Crystallization of Amorphous Silicon. Japanese Journal of Applied Physics, 2007, 46, 6437-6443. | 1.5 | 18 |
| 103 | Ni-imprint induced solid-phase crystallization in Si _{1-x} Ge _x (x: 0≤x<1) on insulator. Applied Physics Letters, 2007, 91, . | 3.3 | 60 |
| 104 | Fabrication of Bistable Prestressed Curved-Beam. , 2007, , . | | 2 |
| 105 | Electrostatic Inkjet Printing of Carbon Nanotube for Cold Cathode Application. , 2007, , . | | 0 |
| 106 | Droplet Ejection Behavior in Electrostatic Inkjet Driving. , 2007, , . | | 0 |
| 107 | Nickel Metal Induced Lateral Crystallization of Patterned Amorphous Silicon Thin Film. Materials Science Forum, 2007, 561-565, 1149-1152. | 0.3 | 4 |
| 108 | Characterization of Gated Cold Cathode Fabrication Using Standing Thin-Film Technique. , 2007, , . | | 0 |

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| 109 | Low-Temperature High-Density Chip-Stack Interconnection Using Compliant Bump. , 2007, , . | | 6 |
| 110 | Orientation Control of Silicon Crystal Grain by Combination of Metal-Induced Solid-Phase Crystallization and Excimer Laser Annealing. The Review of Laser Engineering, 2006, 34, 684-688. | 0.0 | 1 |
| 111 | Application of Microwave Plasma Gate Oxidation to Strained-Si/SiGe-on-Insulator. Japanese Journal of Applied Physics, 2006, 45, 2914-2918. | 1.5 | 1 |
| 112 | Fabrication of a Gated Cold Cathode Using the Inkjet Embedding Method. Japanese Journal of Applied Physics, 2006, 45, 5631-5636. | 1.5 | 1 |
| 113 | Orientation Control of Location-Controlled Si Crystal Grain by Combining Ni Nano-Imprint and Excimer Laser Annealing with Si Double-Layer Process. Japanese Journal of Applied Physics, 2006, 45, L1293-L1295. | 1.5 | 5 |
| 114 | Location and Orientation Control of Si Grain by Combining Metal-Induced Lateral Crystallization and Excimer Laser Annealing. Japanese Journal of Applied Physics, 2006, 45, 4347-4350. | 1.5 | 17 |
| 115 | Properties of Ink-Droplet Formation in Double-Gate Electrospray. Japanese Journal of Applied Physics, 2006, 45, 6475-6480. | 1.5 | 14 |
| 116 | Location Control of Si Thin-Film Grain Using Ni Imprint and Excimer Laser Annealing. Japanese Journal of Applied Physics, 2006, 45, 4335-4339. | 1.5 | 13 |
| 117 | Fabrication of gated cold cathode using standing thin film induced by ion-beam bombardment. Journal of Vacuum Science & Technology B, 2006, 24, 932. | 1.3 | 7 |
| 118 | Combination of Metal Nano-Imprint and Excimer Laser Annealing for Location Control of Si Thin-Film Grain. Materials Research Society Symposia Proceedings, 2006, 910, 5. | 0.1 | 1 |
| 119 | Statistical Investigation on the Design of Field Emitter Array. , 2006, , . | | 0 |
| 120 | Wafer-Level Compliant Bump for 3D Chip-Stacking. International Power Modulator Symposium and High-Voltage Workshop, 2006, , . | 0.0 | 2 |
| 121 | Application of plasma oxidation to strained-Si/SiGe MOSFET. Materials Science in Semiconductor Processing, 2005, 8, 225-230. | 4.0 | 3 |
| 122 | SiGe-collector trench gate insulated gate bipolar transistor fabricated using multiple target sputtering. Solid-State Electronics, 2005, 49, 2006-2010. | 1.4 | 1 |
| 123 | Pyramid Bumps for Fine-Pitch Chip-Stack Interconnection. Japanese Journal of Applied Physics, 2005, 44, 2751-2755. | 1.5 | 13 |
| 124 | Electrostatic Inkjet Patterning Using Si Needle Prepared by Anodization. Japanese Journal of Applied Physics, 2005, 44, 5786-5790. | 1.5 | 17 |
| 125 | Connection Test of Area Bump Using Active-Matrix Switches. Japanese Journal of Applied Physics, 2005, 44, 2770-2773. | 1.5 | 1 |
| 126 | Low-Voltage-Signaling CMOS Receiver with Dynamic Threshold Control. Japanese Journal of Applied Physics, 2005, 44, 2088-2092. | 1.5 | 0 |

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| 127 | Fabrication of Micro Field Emitter Tip Using Ion-Beam Irradiation-Induced Self-Standing of Thin Films. Japanese Journal of Applied Physics, 2005, 44, 5744-5748. | 1.5 | 20 |
| 128 | Electrostatic Droplet Ejection Using Planar Needle Inkjet Head. Japanese Journal of Applied Physics, 2005, 44, 5781-5785. | 1.5 | 15 |
| 129 | Field Electron Emission from Inkjet-Printed Carbon Black. Japanese Journal of Applied Physics, 2004, 43, 3923-3927. | 1.5 | 14 |
| 130 | Breakdown Voltage in Uniaxially Strained n-Channel SOI MOSFET. Japanese Journal of Applied Physics, 2004, 43, 2134-2139. | 1.5 | 9 |
| 131 | Joule Heating of Field EmitterTip Fabricated on Glass Substrate. Japanese Journal of Applied Physics, 2004, 43, 2749-2750. | 1.5 | 5 |
| 132 | A Variable Channel-Size MOSFET with Lightly Doped Drain Structure. Japanese Journal of Applied Physics, 2004, 43, 1763-1767. | 1.5 | 0 |
| 133 | Increased Emission Efficiency of Gated Cold Cathode with Carbonic Nano-Pillars. Japanese Journal of Applied Physics, 2004, 43, 3901-3905. | 1.5 | 1 |
| 134 | CMOS Application of Schottky Source/Drain SOI MOSFET with Shallow Doped Extension. Japanese Journal of Applied Physics, 2004, 43, 2170-2175. | 1.5 | 4 |
| 135 | Cross-Hatch Related Oxidation and Its Impact on Performance of Strained-Si MOSFETs. Japanese Journal of Applied Physics, 2004, 43, 1886-1890. | 1.5 | 12 |
| 136 | Field emission characteristics of defect-controlled polyimide tunneling cathode. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 1353. | 1.6 | 3 |
| 137 | Location Control of Crystal Grains in Excimer Laser Crystallization of Silicon Thin Films for Single-Grain TFTs. Materials Research Society Symposia Proceedings, 2004, 808, 149. | 0.1 | 0 |
| 138 | Si/SiGe heterojunction collector for low loss operation of Trench IGBT. Applied Surface Science, 2004, 224, 399-404. | 6.1 | 11 |
| 139 | Grain positioning using metal imprint technology for single-grain Si thin-film transistor. Electronics and Communications in Japan, 2003, 86, 45-51. | 0.2 | 0 |
| 140 | Structural Properties of Nickel-Metal-Induced Laterally Crystallized Silicon Films. Solid State Phenomena, 2003, 93, 213-218. | 0.3 | 1 |
| 141 | Metal-Induced Lateral Crystallization of Amorphous Silicon under Reduced Nickel Supply. Solid State Phenomena, 2003, 93, 207-212. | 0.3 | 9 |
| 142 | Behavior of Plated Microbumps during Ultrasonic Flip-Chip Bonding Determined from Dynamic Strain Measurement. Japanese Journal of Applied Physics, 2003, 42, 2193-2197. | 1.5 | 19 |
| 143 | CMOS Application of Single-Grain Thin Film Transistor Produced Using Metal Imprint Technology. Japanese Journal of Applied Physics, 2003, 42, 1983-1987. | 1.5 | 14 |
| 144 | Structural Properties of Nickel Metal-Induced Laterally Crystallized Silicon Films and Their Improvement Using Excimer Laser Annealing. Japanese Journal of Applied Physics, 2003, 42, 2592-2599. | 1.5 | 17 |

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| 145 | Field emission from metal particles bound with a photoresist. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 552. | 1.6 | 6 |
| 146 | Micro Field Emitter with Nano-Pillarets Formed by Reactive Ion Etching of Photoresist. Japanese Journal of Applied Physics, 2003, 42, 4054-4058. | 1.5 | 2 |
| 147 | Schottky Source/Drain SOI MOSFET with Shallow Doped Extension. Japanese Journal of Applied Physics, 2003, 42, 2009-2013. | 1.5 | 40 |
| 148 | In situ observation of nickel metal-induced lateral crystallization of amorphous silicon thin films. Applied Physics Letters, 2002, 80, 944-946. | 3.3 | 77 |
| 149 | CMOS Image Sensor Using SOI-MOS/Photodiode Composite Photodetector Device. Japanese Journal of Applied Physics, 2002, 41, 2620-2624. | 1.5 | 6 |
| 150 | Fabrication of Single-Crystal Silicon Field Emitter Array on Glass Substrate. Japanese Journal of Applied Physics, 2002, 41, 4307-4310. | 1.5 | 5 |
| 151 | Easy Release of Mold in Imprint Lithography Using Ion-Beam-Irradiated Photoresist Surface. Japanese Journal of Applied Physics, 2002, 41, 4190-4193. | 1.5 | 1 |
| 152 | Influence of Direct Au-Bump Formation on Metal Oxide Semiconductor Field Effect Transistor. Japanese Journal of Applied Physics, 2002, 41, 2714-2719. | 1.5 | 13 |
| 153 | Physical Random-Number Generator Using Schottky MOSFET. Japanese Journal of Applied Physics, 2002, 41, 2306-2311. | 1.5 | 7 |
| 154 | SOI-MOSFET/Diode Composite Photodetection Device. Japanese Journal of Applied Physics, 2001, 40, 2897-2902. | 1.5 | 5 |
| 155 | Dynamic Strain and Chip Damage during Ultrasonic Flip Chip Bonding. Japanese Journal of Applied Physics, 2001, 40, 3044-3048. | 1.5 | 16 |
| 156 | Monitoring of Two-Dimensional Plasma Uniformity with Electrostatic Probing of Oxidized Wafer Surface. Japanese Journal of Applied Physics, 2001, 40, L327-L329. | 1.5 | 0 |
| 157 | Stamp technology for fabrication of field emitter from organic material. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 877. | 1.6 | 7 |
| 158 | New SOI Complementary-Bipolar Complementary-MOS (CBiCMOS) with Merged Device Structure. Japanese Journal of Applied Physics, 2000, 39, 2241-2245. | 1.5 | 0 |
| 159 | Measurement of Dynamic Strain during Ultrasonic Au Bump Formation on Si Chip. Japanese Journal of Applied Physics, 2000, 39, 2478-2482. | 1.5 | 9 |
| 160 | Imprint Lithography Using Triple-Layer-Resist and Its Application to Metal-Oxide-Silicon Field-Effect-Transistor Fabrication. Japanese Journal of Applied Physics, 2000, 39, 7080-7085. | 1.5 | 10 |
| 161 | Dehydration after Plasma Oxidation of Porous Low-Dielectric-Constant Spin-on-Glass Films. Japanese Journal of Applied Physics, 2000, 39, 3919-3923. | 1.5 | 23 |
| 162 | Enhanced nucleation in solid-phase crystallization of amorphous Si by imprint technology. Applied Physics Letters, 2000, 76, 3774-3776. | 3.3 | 49 |

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| 163 | Fabrication of Carbon-Based Field Emitters Using Stamp Technology. Japanese Journal of Applied Physics, 1999, 38, 7203-7207. | 1.5 | 18 |
| 164 | A New Merged Bipolar-MOS Transistor in a Silicon on Insulator Structure. Japanese Journal of Applied Physics, 1999, 38, 2501-2505. | 1.5 | 1 |
| 165 | Field Emission from an Ion-Beam-Modified Polyimide Film. Japanese Journal of Applied Physics, 1999, 38, L261-L263. | 1.5 | 20 |
| 166 | Electrical properties of homoepitaxial boron-doped diamond thin films grown by chemical vapor deposition using trimethylboron as dopant. Diamond and Related Materials, 1999, 8, 42-47. | 3.9 | 7 |
| 167 | Morphology and semiconducting properties of homoepitaxially grown phosphorus-doped (100) and (111) diamond films by microwave plasma-assisted chemical vapor deposition using triethylphosphine as a dopant source. Journal of Crystal Growth, 1998, 191, 723-733. | 1.5 | 9 |
| 168 | Growth behavior of boron-doped diamond in microwave plasma-assisted chemical vapor deposition using trimethylboron as the dopant source. Diamond and Related Materials, 1998, 7, 88-95. | 3.9 | 24 |
| 169 | Fabrication of Field Emitter Arrays Using Si Delamination by Hydrogen Ion Implantation. Japanese Journal of Applied Physics, 1998, 37, 7138-7142. | 1.5 | 0 |
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